CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail, with sufficient postage, in an envelope addressed to: Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-1450, on the below date: Name: Anthony P. Curtis, Ph.D., 46,193 Signature:

BRINKS HOFER GILSON &LIONE

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Appln. of:	Kuang Chien et al.
Appln. No.:	10/680,509
Filed:	October 7, 2003

For:

Adhesive Bonding with Low Temperature Grown Amorphous or Polycrystalline

Compound Semiconductor

Attorney Docket No: 10322/57

Mail Stop Amendment **Commissioner for Patents** P. O. Box 1450 Alexandria, VA 22313-1450

**TRANSMITTAL** 

Examiner: Hoa B. Trinh

Art Unit: 2814

		•									
Sir:											
Attac	Attached is/are:										
$\boxtimes$	☐ Transmittal Cover Letter (1p. Filed in Dup.); Supplemental Information Disclosure Statement and PTO Form 1449 (3pp.); 6 Non-U.S. Prior Art (B5-B10)										
$\boxtimes$	Return Receipt Postcard										
Fee c	alc	ulation:									
$\boxtimes$	N	o additional fee is re	quired.								
	S	mall Entity.									
	Ai	n extension fee in ar	n amour	nt of \$ for a _	mont	h	extensior	n of time un	der 3	37 C.F.R.	§ 1.136(a).
	Α	petition or processir	ng fee ir	n an amount of \$	under :	37	C.F.R. §	3 1.17(	_).		
	A	n additional filing fee	has be	een calculated as sh	nown below	<b>v</b> :					
							Sma	III Entity		Not a S	mall Entity
		Claims Remaining After Amendment		Highest No. Previously Paid For	Present Extra		Rate	Add'l Fee	or	Rate	Add'l Fee
Total			Minus				x \$25=			x \$50=	
Indep.			Minus				x 100=			x \$200=	
First P	res	entation of Multiple De	p. Claim				+\$180=			+ \$360=	
							Total	\$		Total	\$
Fee p	ay	ment:									
	Α	check in the amoun	t of \$	is enclosed.							
	Please charge Deposit Account No. 23-1925 in the amount of \$ . A copy of this Transmittal is enclosed for this purpose.										
	P	ayment by credit car	d in the	amount of \$	(Form PTC	<b>)</b> -	2038 is a	ittached).			
	· · ·										
	7/26/or Respectfully submitted										
Date	;		•		Antho	'n	y P. Curti	s, Ph.D. (R	eg. N	No. 46,19	3)

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Appln. of: Kuang Chien ET AL.

Appln. No.: 10/680,509

Filed: October 7, 2003

For: ADHESIVE BONDING WITH

LOW TEMPERATURE GROWN

AMORPHOUS OR POLYCRYSTALLINE

COMPOUND

SEMICONDUCTOR

Attorney Docket No: 10322/57

Examiner: Hoa B. Trinh

Art Unit: 2814

## SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

In accordance with the duty of disclosure under 37 C.F.R. §1.56 and §§1.97-1.98, and more particularly in accordance with 37 C.F.R. §1.97(c), Applicants hereby cite the following reference(s):

No.	Date of Publication	Patentee/Applicant/Assignee			
5,920,766	July 6, 1999	Floyd			
5,858,855	January 12, 1999	Kobayashi			
5,854,090	December 29, 1998	lwai et al.			
5,233,216	August 3, 1993	Inoue et al.			
	FOREIGN PATENT DO	CUMENTS			
EP 1 246 238 A2	October 2, 2002	EPO			
JP 10-12506	January 16, 1998	Japan			
	R ART - NON PATENT LITE				
Copy of International Search Report from corresponding PCT patent application number					
PCT/US2004/031254.					
K.L. Chang, G.W. Pick	krell, K.Y. Cheng and K.C. Hs	ieh, Wafer Bonding With Low-			
Temperature-Grown (	Ga,P) as an Adhesive Materia	al, pgs. 906-910, Institute of Physics			
	uctor Science and Technology				
K.D. Choquette, K.M.	Geib, B. Roberds, H.Q. Hou,	R.D. Twesten and B.E. Hammons,			
Short Wavelength Bottom-Emitting Vertical Cavity Lasers Fabricated Using Wafer					
Bonding, pgs. 1404-1405, IEEE, Electronic Letters, Vol. 34, No. 14, July 9, 1998.					
K. Mori, K. Tokutome and S. Sugou, Low-Threshold Pulsed Operation of Long-wavelength					
Lasers on Si Fabricated By Direct Bonding, pgs. 284-285, IEEE Electronic Letters, Vol. 31,					
No. 4, February 16, 1995.					

Applicants are enclosing Form PTO-1449 (one sheet), along with a copy of each listed reference for which a copy is required under 37 C.F.R. §1.98(a)(2). As each of the listed references is in English, no further commentary is believed to be necessary, 37 C.F.R §1.98(a)(3). Applicants respectfully request the Examiner's

consideration of the above reference(s) and entry thereof into the record of this application.

By submitting this Statement, Applicants are attempting to fully comply with the duty of candor and good faith mandated by 37 C.F.R. §1.56. As such, this Statement is not intended to constitute an admission that any of the enclosed references, or other information referred to therein, constitutes "prior art" or is otherwise "material to patentability," as that phrase is defined in 37 C.F.R. §1.56(a).

For purposes of 37 C.F.R. §1.704(d), Applicants certify that each item of information contained in this Statement was first cited in any communication from a foreign patent office in a counterpart application, and that this communication was not received by any individual designated in 37 C.F.R. §1.56(c) more than thirty days prior to the filing of this Statement (a copy of any foreign communication first citing a listed reference is attached for the Examiner's reference).

Applicants certify pursuant to 37 C.F.R. §1.97(e)(1) that each item of information in this Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Statement (a copy of any foreign communication first citing a listed reference is attached for the Examiner's reference). Accordingly, Applicants have calculated no fee to be due in connection with the filing of this Statement. However, the Director is authorized to charge any fee deficiency associated with the filing of this Statement to a deposit account, as authorized in the Transmittal accompanying this Statement.

7/26/05

Date

Respectfully submitted,

Anthony P. Curtis, Ph.D.

(Reg. No. 46,193)

(VFORM®) 0-1449	SERIAL NO.	CASE NO.
a Inhe	10/680,509	10322/57
LIST OF PATENTS AND PUBLICATIONS FOR	FILING DATE	GROUP ART UNIT
APPLICANT'S INFORMATION DISCLOSURE STATEMENT	October 7, 2003	2814
(use several sheets if necessary)	APPLICANT(S): Kuang Chien e	t al.

REFERENCE DESIGNATION

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EXAMINER INITIAL		DOCUMENT NUMBER Number-Kind Code (if known)	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
	B1	5,920,766	July 6, 1999	Floyd		
	B2	5,858,855	January 12, 1999	Kobayashi		
<del></del>	В3	5,854,090	December 29, 1998	lwai et al.		
	B4	5,233,216	August 3, 1993	Inoue et al.		

## **FOREIGN PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER Number-Kind Code (If known)	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES OR NO
	B5	EP 1 246 238 A2	October 2, 2002	EPO		
	B6	JP 10-12506	January 16, 1998	Japan		

EXAMINER INITIAL	OTHER ART — NON PATENT LITERATURE DOCUMENTS  (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.						
	B7	Copy of International Search Report from corresponding PCT patent application number PCT/US2004/031254.					
	B8	K.L. Chang, G.W. Pickrell, K.Y. Cheng and K.C. Hsieh, Wafer Bonding With Low-Temperature- Grown (Ga,P) as an Adhesive Material, pgs. 906-910, Institute of Physics Publishing, Semiconductor Science and Technology, 2004					
	B9	K.D. Choquette, K.M. Geib, B. Roberds, H.Q. Hou, R.D. Twesten and B.E. Hammons, Short Wavelength Bottom-Emitting Vertical Cavity Lasers Fabricated Using Wafer Bonding, pgs. 1404-1405, IEEE, Electronic Letters, Vol. 34, No. 14, July 9, 1998.					
	B10	K. Mori, K. Tokutome and S. Sugou, Low-Threshold Pulsed Operation of Long-wavelength Lasers on Si Fabricated By Direct Bonding, pgs. 284-285, IEEE Electronic Letters, Vol. 31, No. 4, February 16, 1995.					

EXAMINER	DATE CONSIDERED
	·

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.